

# Dongsuk Lim

## List of Publications by Year in descending order

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11  
papers

411  
citations

1040056

9  
h-index

1281871

11  
g-index

11  
all docs

11  
docs citations

11  
times ranked

966  
citing authors

#	ARTICLE	IF	CITATIONS
1	Gate Tunable Self-Biased Diode Based on Few Layered MoS <sub>2</sub> and WSe <sub>2</sub> . Chemistry of Materials, 2018, 30, 1011-1016.	6.7	20
2	Tunable Electron and Hole Injection Enabled by Atomically Thin Tunneling Layer for Improved Contact Resistance and Dual Channel Transport in MoS <sub>2</sub> /WSe <sub>2</sub> van der Waals Heterostructure. ACS Applied Materials & Interfaces, 2018, 10, 23961-23967.	8.0	17
3	Photodetector Based on Multilayer SnSe <sub>2</sub> Field Effect Transistor. Journal of Nanoscience and Nanotechnology, 2018, 18, 4243-4247.	0.9	14
4	Observation of negative differential resistance in mesoscopic graphene oxide devices. Scientific Reports, 2018, 8, 7144.	3.3	25
5	Tunable electrical properties of multilayer HfSe <sub>2</sub> field effect transistors by oxygen plasma treatment. Nanoscale, 2017, 9, 1645-1652.	5.6	38
6	Junctionless Diode Enabled by Self-Bias Effect of Ion Gel in Single-Layer MoS <sub>2</sub> Device. ACS Applied Materials & Interfaces, 2017, 9, 26983-26989.	8.0	8
7	P-doping and efficient carrier injection induced by graphene oxide for high performing WSe <sub>2</sub> rectification devices. Applied Physics Letters, 2016, 108, .	3.3	8
8	Gate-Tunable Hole and Electron Carrier Transport in Atomically Thin Dual-Channel WSe <sub>2</sub> /MoS <sub>2</sub> Heterostructure for Ambipolar Field-Effect Transistors. Advanced Materials, 2016, 28, 9519-9525.	21.0	70
9	High performance MoS <sub>2</sub> -based field-effect transistor enabled by hydrazine doping. Nanotechnology, 2016, 27, 225201.	2.6	11
10	Tunable Electrical and Optical Characteristics in Monolayer Graphene and Few-Layer MoS <sub>2</sub> Heterostructure Devices. Nano Letters, 2015, 15, 5017-5024.	9.1	150
11	Electrical characterization of multilayer HfSe <sub>2</sub> field-effect transistors on SiO <sub>2</sub> substrate. Applied Physics Letters, 2015, 106, .	3.3	50